MOTOR® MA供应商 SEMICONDUCTOR TECHNICAL DATA

捷多邦,专业PCB打样工厂,24小时加急出货

by MRF1090MA/D

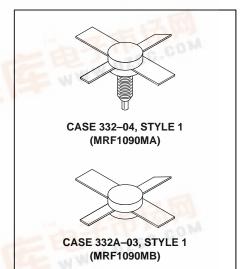
The RF Line Microwave Pulse Power Transistors

Designed for Class B and C common base amplifier applications in short pulse TACAN, IFF, and DME transmitters.

- Guaranteed Performance @ 1090 MHz, 50 Vdc Output Power = 90 Watts Peak Minimum Gain = 8.4 dB
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Industry Standard Package
- Nitride Passivated
- Gold Metallized for Long Life and Resistance to Metal Migration
- Internal Input Matching for Broadband Operation
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.



90 W PEAK, 960–1215 MHz MICROWAVE POWER TRANSISTORS NPN SILICON



MAXIMUM RATINGS

| | and the second se | | |
|---|---|-------------|---------------|
| Rating | Symbol | Value | Unit |
| Collector-Base Voltage | VCBO | 70 | Vdc |
| Emitter-Base Voltage | VEBO | 4.0 | Vdc |
| Collector–Current — Peak (1) | IC | 6.0 | Adc |
| Total Device Dissipation @ T _C = 25°C (1) (2) Derate above 25°C | PD | 290 1.66 | Watts W/°C |
| Storage Temperature Range | T _{stg} | -65 to +150 | °C |

THERMAL CHARACTERISTICS

| Characteristic | | Мах | Unit |
|--|------------------|-----|------|
| Thermal Resistance, Junction to Case (3) | R _{θJC} | 0.6 | °C/W |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|-----------------------|-----|-------|-------|--------|
| OFF CHARACTERISTICS | • | | | -510 | Cert . |
| Collector–Emitter Breakdown Voltage ($I_C = 25 \text{ mAdc}, V_{BE} = 0$) | V _(BR) CES | 70 | ET. | DZSC. | Vdc |
| Collector–Base Breakdown Voltage (I _C = 25 mAdc, I _E = 0) | V(BR)CBO | 70 | AT AL | - | Vdc |
| Emitter–Base Breakdown Voltage (I _E = 5.0 mAdc, I _C = 0) | V _{(BR)E} BO | 4.0 | — | - | Vdc |
| Collector Cutoff Current $(V_{CB} = 50 \text{ Vdc}, I_E = 0)$ | ІСВО | — | _ | 5.0 | mAdc |
| ON CHARACTERISTICS | • | | • | • | • |
| DC Current Gain (4) | hee | 10 | 30 | _ | _ |

| | ''FE | |
|---|------|--|
| (I _C = 2.5 Adc, V _{CE} = 5.0 Vdc) | | |

NOTES:

frevsc.com

1. Pulse Width = 10 μ s, Duty Cycle = 1%.

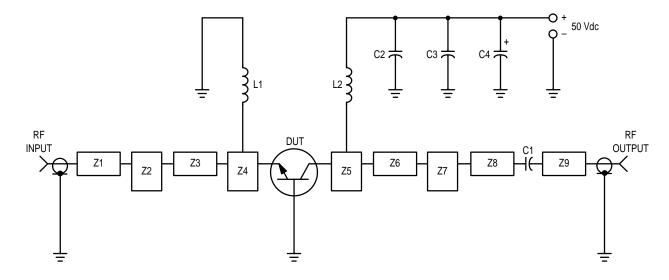
These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers.
Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.
80 µs Pulse on Tektronix 576 or equivalent.



(continued)

| Characteristic | Symbol | Min | Тур | Max | Unit | | |
|--|-----------------|--------------------------------|------|-----|------|--|--|
| DYNAMIC CHARACTERISTICS | | | | | | | |
| Output Capacitance ($V_{CB} = 50 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$) | C _{ob} | - | 12 | 16 | pF | | |
| FUNCTIONAL TESTS (Pulse Width = 10 µs, Duty Cycle = 1.0% |) | - | - | | | | |
| Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz) | GPB | 8.4 | 10.8 | _ | dB | | |
| Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz) | η | 35 | 40 | _ | % | | |
| Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz, VSWR = 10:1 All Phase Angles) | Ψ | No Degradation in Power Output | | | | | |

ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^{\circ}C$ unless otherwise noted)



C1, C2 — 220 pF Chip Capacitor, 100–mil ATC C3 — 0.1 μ F C4 — 47 μ F/75 V L1, L2 — 3 Turns #18 AWG, 1/8″ ID Z1–Z9 — Distributed Microstrip Elements,

See Photomaster

Board Material — 0.031" Thick Glass Teflon, ϵ_{f} = 2.5



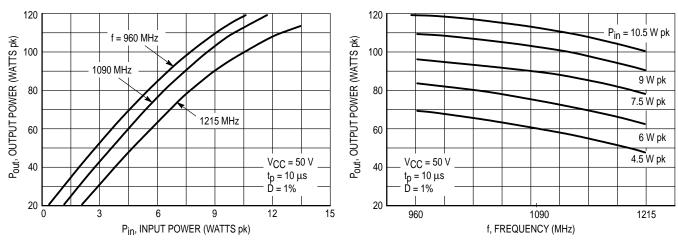




Figure 3. Output Power versus Frequency

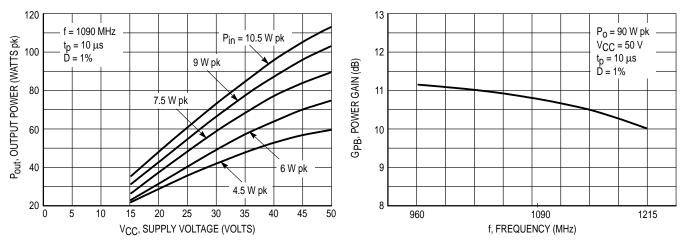
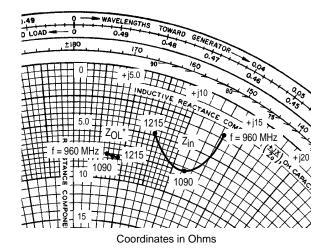


Figure 4. Output Power versus Supply Voltage

Figure 5. Power Gain versus Frequency



| | = 90 W pk p = 10 μs | |
|---|------------------------|-------------------|
| f | Z _{in} | Z _{OL} * |

| f | Z _{in} | Z _{OL} * |
|------|-----------------|-------------------|
| MHz | Ohms | Ohms |
| 960 | 2.8 + j13.2 | 7.6 + j3.5 |
| 1090 | 7.4 + j11.4 | 7.6 + j4.0 |
| 1215 | 4.7 + j7.5 | 7.7 + j4.5 |

Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage, and frequency.



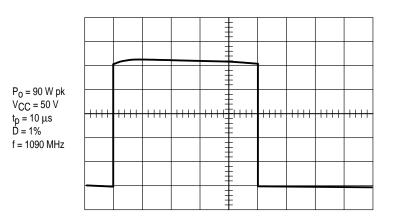
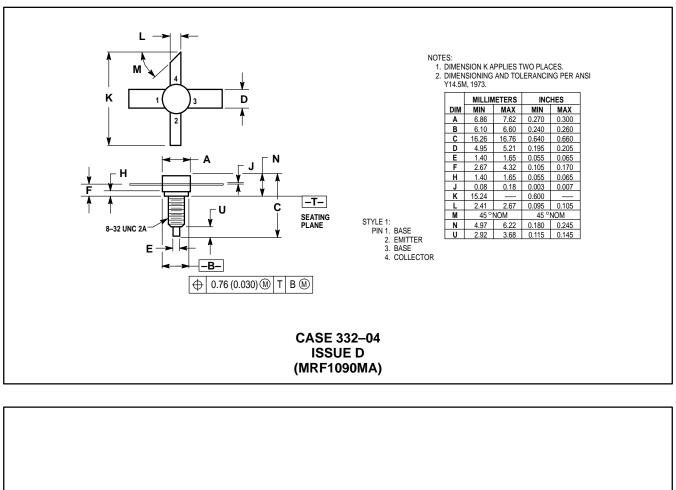
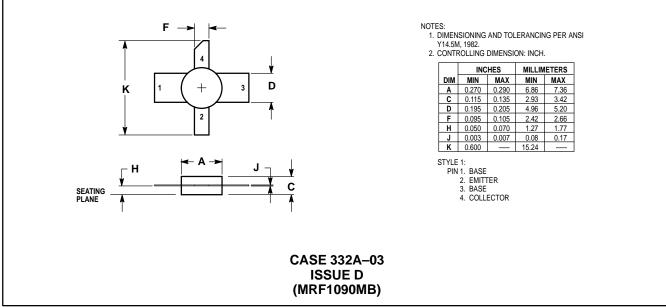


Figure 7. Typical Pulse Performance

PACKAGE DIMENSIONS





Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and ᠺ are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado 80217. 303-675-2140 or 1-800-441-2447 Mfax is a trademark of Motorola, Inc.

Mfax™: RMFAX0@email.sps.mot.com - TOUCHTONE 602-244-6609

INTERNET: http://motorola.com/sps

- US & Canada ONLY 1-800-774-1848

MOTOROLA

Nishi-Gotanda, Shinagawa-ku, Tokyo 141, Japan. 81-3-5487-8488

JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 4-32-1,

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298